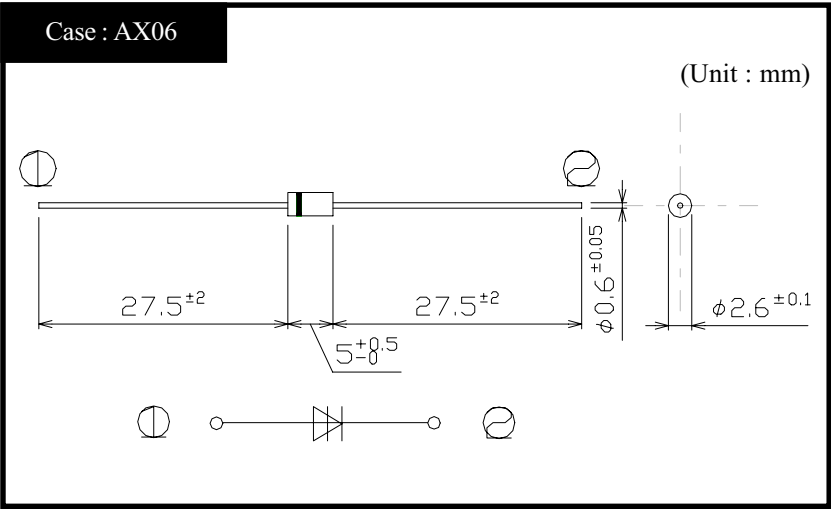


G1V(A)10C

OUTLINE DIMENSIONS



RATINGS

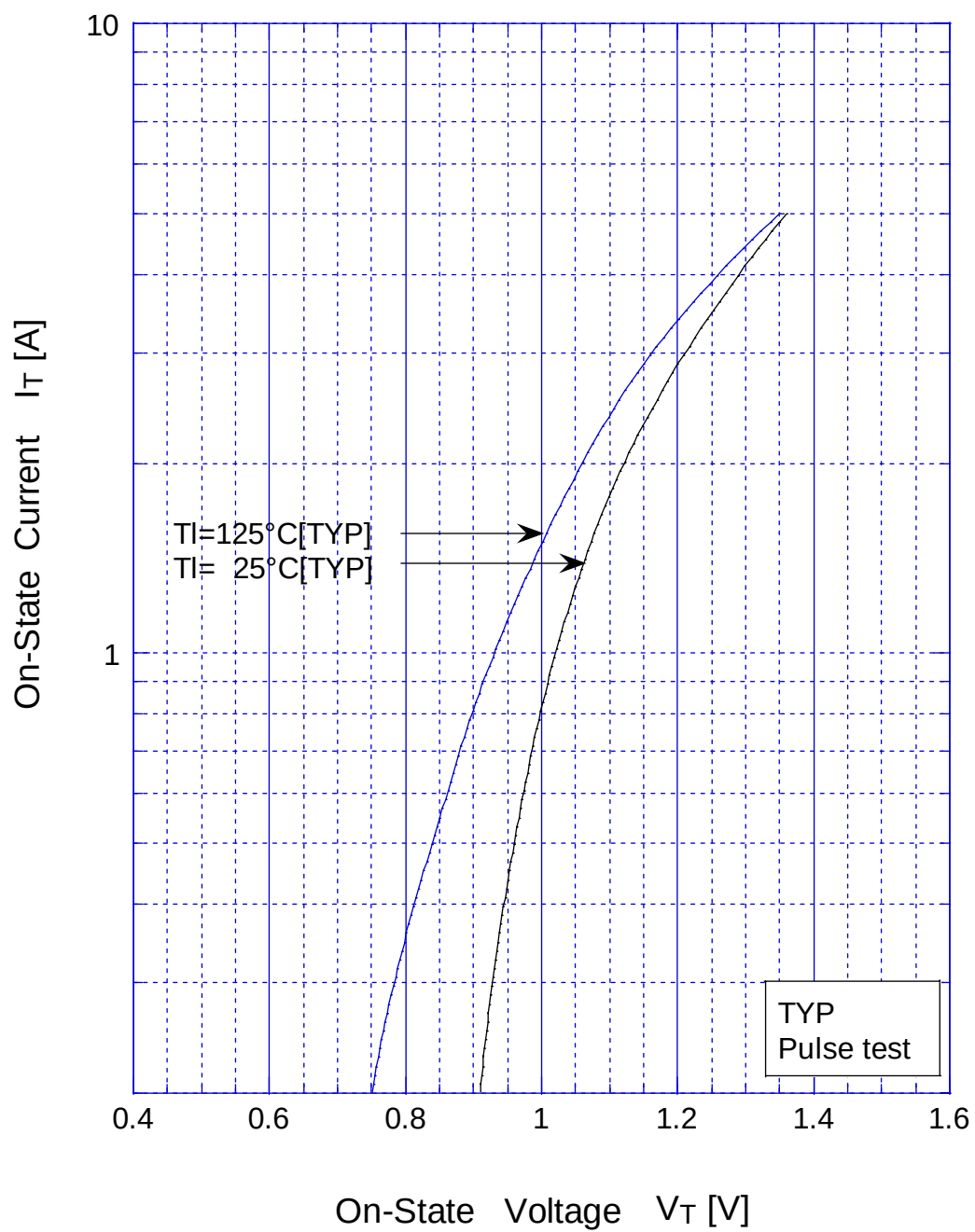
Absolute Maximum Ratings (Unless otherwise specified, Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-40~125	°C
Operating Junction Temperature	Tj		125	°C
Maximum Off-state Voltage	V _{DRM(A)}		90	V
RMS On-state Current	I _T	Tl = 98°C, 50Hz Sine wave (θ = 180°)	1	A
Pulse On-state Current	I _{TRM}	Ta = 25 °C, Pulse width 10 μ s, 60 Hz Sine wave	80	A
Critical Rate of Rise of On-state Current	di _T /dt		80	A/μ s

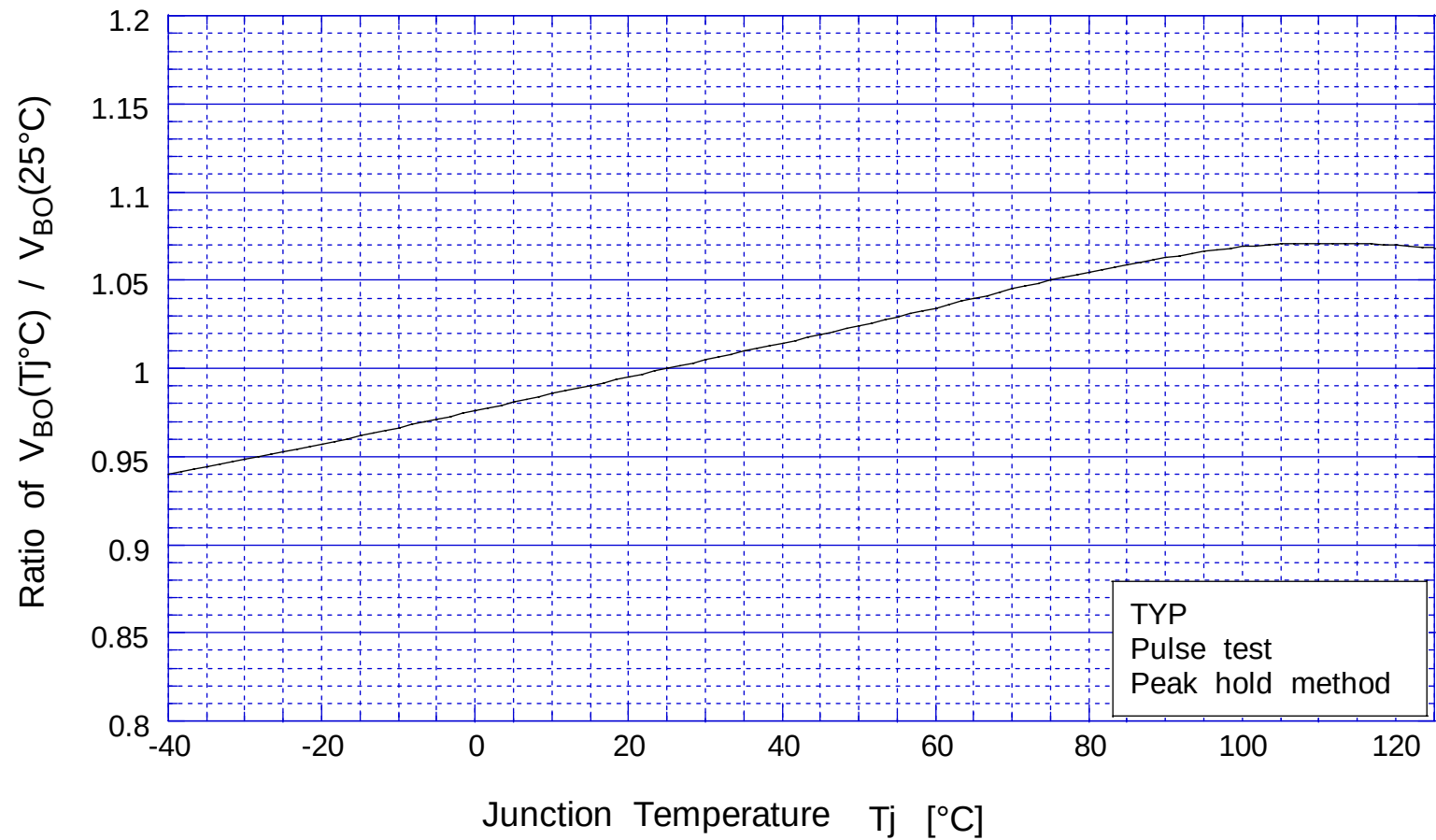
Electrical Characteristics (Unless otherwise specified, Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V _{BO(A)}	Pulse measurement (dv/dt = 4V/ms)	Min 95 Max 110	V
Off-state Current	I _{DRM(A)}	V _D = V _{DRM(A)}	Max 10	μ A
Breakover Current	I _{BO(A)}		Max 0.5	mA
Holding Current	I _{H(A)} I _{H(K)}		Max 60	mA
On-state Voltage	V _{T(A)} V _{T(K)}	I _T = 1A I _T = 1A	Max 1.5	V
Switching Resistance	R _{S(A)}		Min 0.1	kΩ
Thermal Resistance	θ j l	Junction to lead	Max 20	°C/W

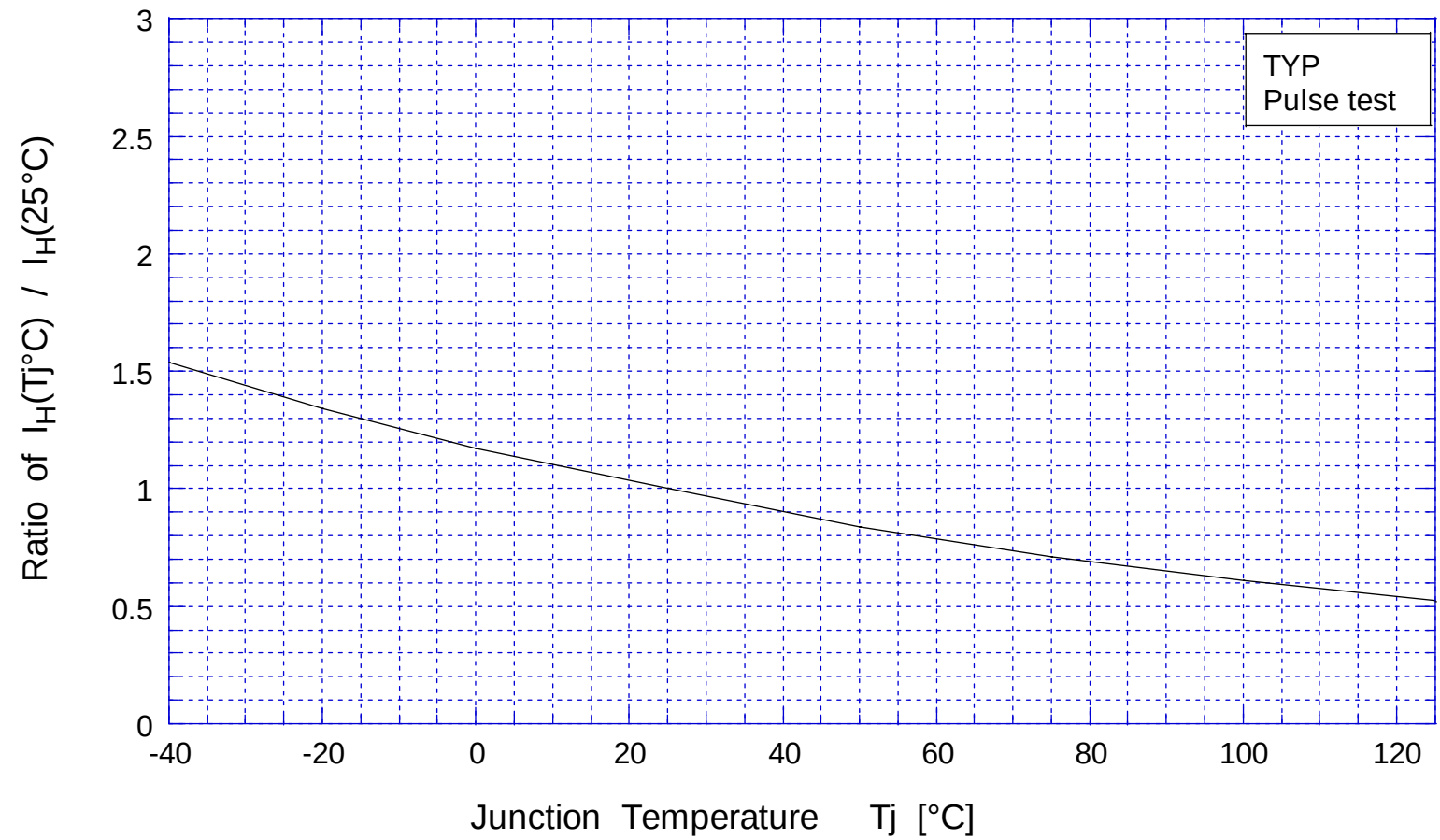
G1V(A)10C On-State Voltage - On-State Current



G1V(A)10C Break Over Voltage - Junction Temperature



G1V(A)10C Holding Current - Junction Temperature



G1V(A)10C Pulse On-state Current Rating

